

# NPN SILICON POWER TRANSISTORS

The 2N6676, 2N6677 and 2N6678 transistor are designed for high voltage switching applications such as:

## FEATURES

- \*Off-Line Power Supplies
- \*Converter Circuits
- \*Pulse Width Modulated Regulators
- Specification Feature-  
High Voltage Capability
- Fast Switching Speeds
- Low Saturation Voltage

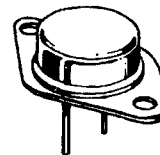
Boca Semiconductor Corp.

**NPN**  
**2N6676**  
**2N6677**  
**2N6678**

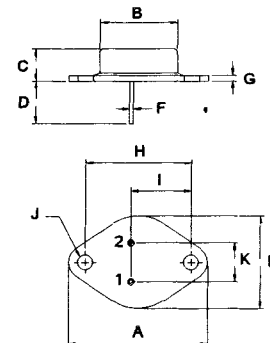
**15 AMPERE**  
**NPN SILICON**  
**POWER TRANSISTORS**  
**300-400 VOLTS**  
**175 WATTS**

## MAXIMUM RATINGS

Characteristic	Symbol	2N6676	2N6677	2N6678	Unit
Collector-Emitter Voltage	$V_{CEV}$	450	550	650	V
Collector-Emitter Voltage	$V_{CEX}$	350	400	450	V
Collector-Emitter Voltage	$V_{CEO}$	300	350	400	V
Emitter-Base Voltage	$V_{EBO}$	8.0			V
Collector Current - Continuous	$I_C$	15			A
Collector Current - Peak	$I_{CM}$	20			
Base Current-Peak	$I_B$	5.0			A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_T$	175			W
Operating and Storage Junction Temperature Range	$T_J, T_{STG}$	-65 to +200			$^\circ\text{C}$



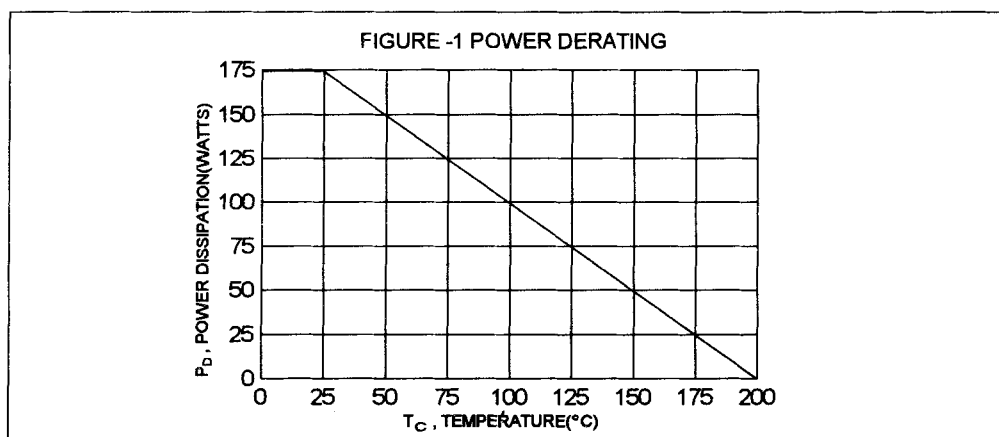
TO-3



PIN 1. BASE  
2. EMITTER  
COLLECTOR(CASE)

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	UNIT
Thermal Resistance Junction to Case	$R_{\theta jc}$	1.0	$^\circ\text{C/W}$



DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18

ELECTRICAL CHARACTERISTICS (  $T_c = 25^\circ\text{C}$  unless otherwise noted )

Characteristic	Symbol	Min	Max	Unit
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## OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage(1) ( $I_C = 200\text{ mA}$ , $I_B = 0$ )	2N6676 2N6677 2N6678	$V_{CEO(sus)}$	300 350 400	V
Collector Cutoff Current ( $V_{CE} = \text{Rated } V_{CEV}$ , $V_{BE(off)} = -1.5\text{V}$ ) ( $V_{CE} = \text{Rated } V_{CEV}$ , $V_{BE(off)} = -1.5\text{V}$ , $T_c = 100^\circ\text{C}$ )		$I_{CEV}$	0.1 1.0	mA
Emitter Cutoff Current ( $V_{EB} = 8.0\text{ V}$ , $I_C = 0$ )		$I_{EBO}$	2.0	mA

## ON CHARACTERISTICS (1)

DC Current Gain ( $I_C = 15\text{ A}$ , $V_{CE} = 3.0\text{ V}$ )		$h_{FE}$	8.0	
Collector-Emitter Saturation Voltage ( $I_C = 15\text{ A}$ , $I_B = 3.0\text{ A}$ )		$V_{CE(sat)}$	1.5	V
Base-Emitter Saturation Voltage ( $I_C = 15\text{ A}$ , $I_B = 3.0\text{ A}$ )		$V_{BE(sat)}$	1.5	V

## DYNAMIC CHARACTERISTICS

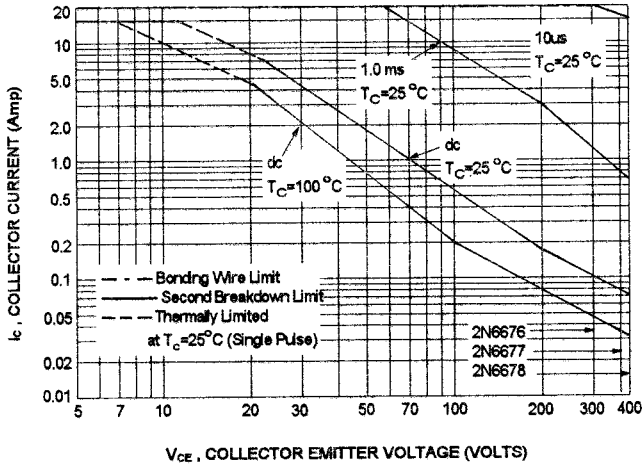
Current - Gain - Bandwidth Product (2) ( $I_C = 1.0\text{ A}$ , $V_{CE} = 10\text{ V}$ , $f = 5.0\text{ MHz}$ )		$F_T$	3.0	MHz
Output Capacitance ( $I_C = 1.0\text{ A}$ , $V_{CB} = 10\text{ V}$ , $f = 0.1\text{ MHz}$ )		$C_{ob}$	500	pF

## SWITCHING CHARACTERISTICS

Delay Time	$V_{CC} = 200\text{V}$ , $I_C = 15\text{A}$ $I_{B1} = I_{B2} = 3\text{A}$ , $t_p = 20\mu\text{s}$ Duty Cycle $\leq 2\%$ $V_{BB} = 6\text{V}$ , $R_L = 13.5\Omega$ $T_c = 25^\circ\text{C}$	$t_d$	0.2	us
Rise Time		$t_r$	0.6	us
Storage Time		$t_s$	2.5	us
Fall Time		$t_f$	0.6	us

(1) Pulse Test: Pulse width = 300 us , Duty Cycle  $\leq 2.0\%$ (2)  $f_T = |h_{fe}| \cdot f_{test}$

FIG-2 FORWARD BIAS SAFE OPERATING AREA

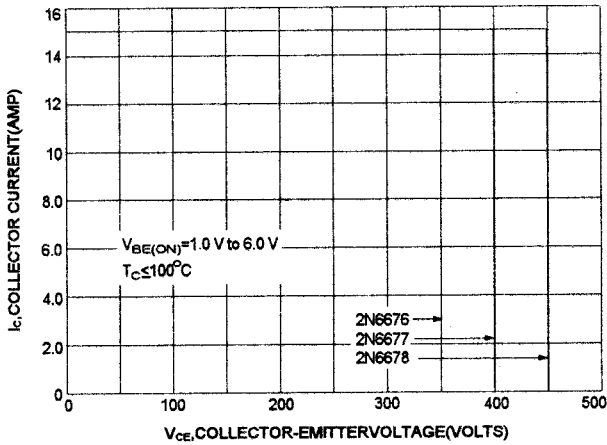


**FORWARD BIAS**

There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate  $I_c$ - $V_{ce}$  limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of FIG-2 is base on  $T_c = 25^\circ C$ ;  $T_{j(pk)}$  is variable depending on power level. second breakdown pulse limits are valid for duty cycles to 10% provided  $T_c \geq 25^\circ C$ , At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

FIG-3 REVERSE BIAS SAFE OPERATING AREA



**REVERSE BIAS**

For inductive loads, high voltage and high current must be sustained simultaneously during turn-off, in most cases, with the base-to-emitter junction reverse biased. Under these conditions the collector voltage must be held to a safe level at or below a specific value of collector current. This can be accomplished by several means such as active clamping, RC snubbing, load line shaping, etc. the safe level for these devices is specified as Reverse Bias Safe Operating Area and represents the voltage-current condition allowable during reverse biased turn-off. This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode. FIG-3 gives the RBSOA characteristics.